

A two-temperature model of radiation damage in α -quartz

Carolyn L. Phillips¹, Rudolph Magyar²,
Paul S. Crozier²

¹Applied Physics, University of Michigan

²Multiscale Material Modeling Department, Sandia National
Laboratories

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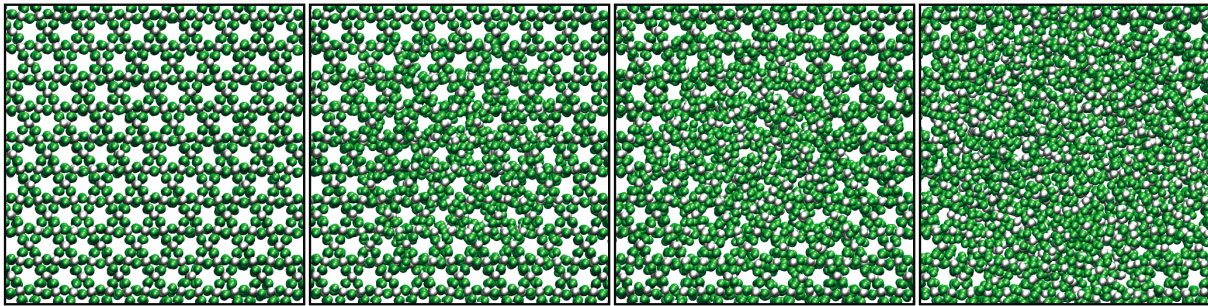
Molecular Dynamics used to Model Material Responses

- **Quantum MD**
 - Includes electronic degrees of freedom
 - limited to small system sizes.
- **Classical MD**
 - simpler (pair-wise) interactions between point atoms
 - larger system

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Modeling Large Systems with “Coarse” Electronic Transport

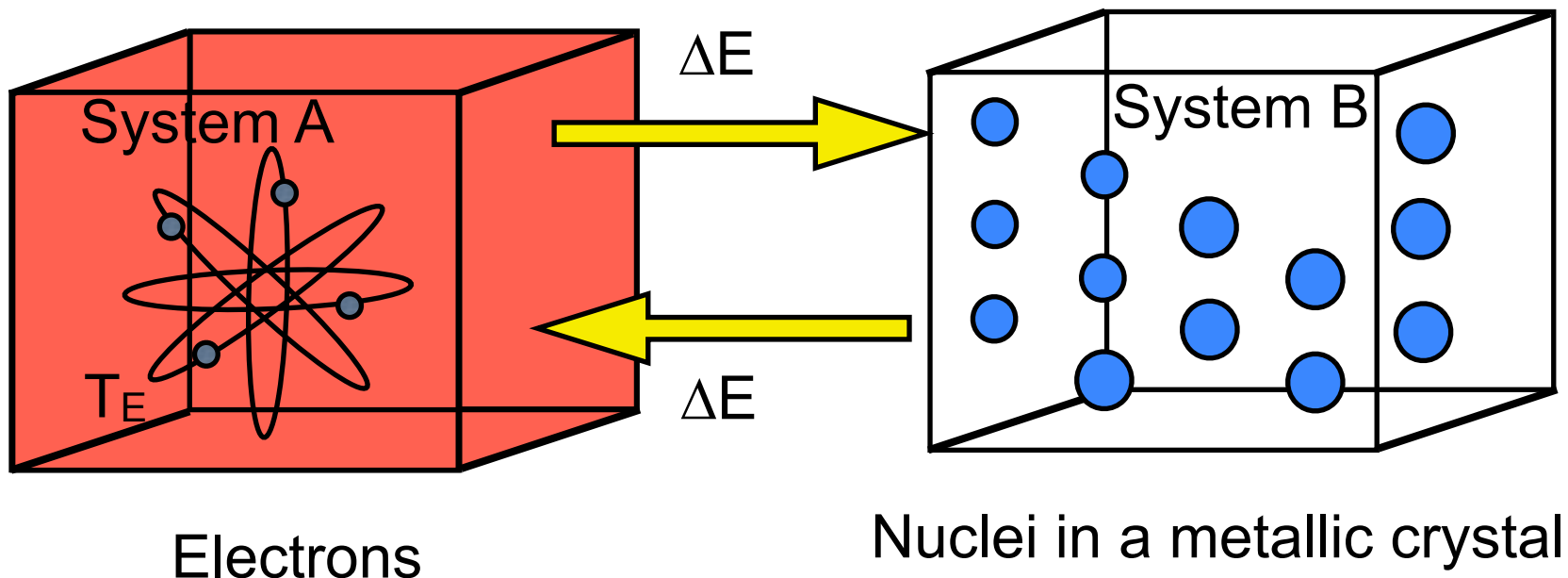
- potentials adequate to capture non-equilibrium behavior
- energy losses due to inelastic scattering by electrons?



*Local material response is **Temperature Dependent**.
The rate at which energy is transported can have a
significant effect on the material response*

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What is a Two Temperature Model (TTM)?

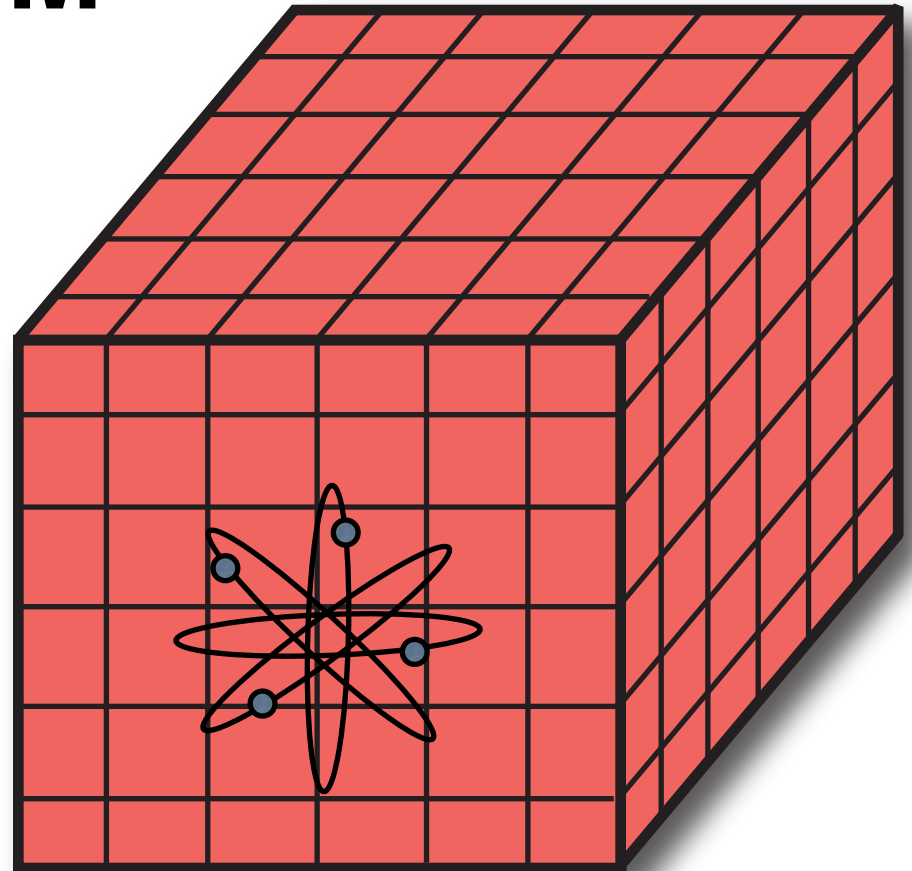


- Rapid Heat Deposition (laser, radiation, etc.)
- Electrons and Nuclei are out-of-equilibrium
- Electrons Delocalized
- Heat transfer through the electronic subsystem is non-negligible

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History of TTM

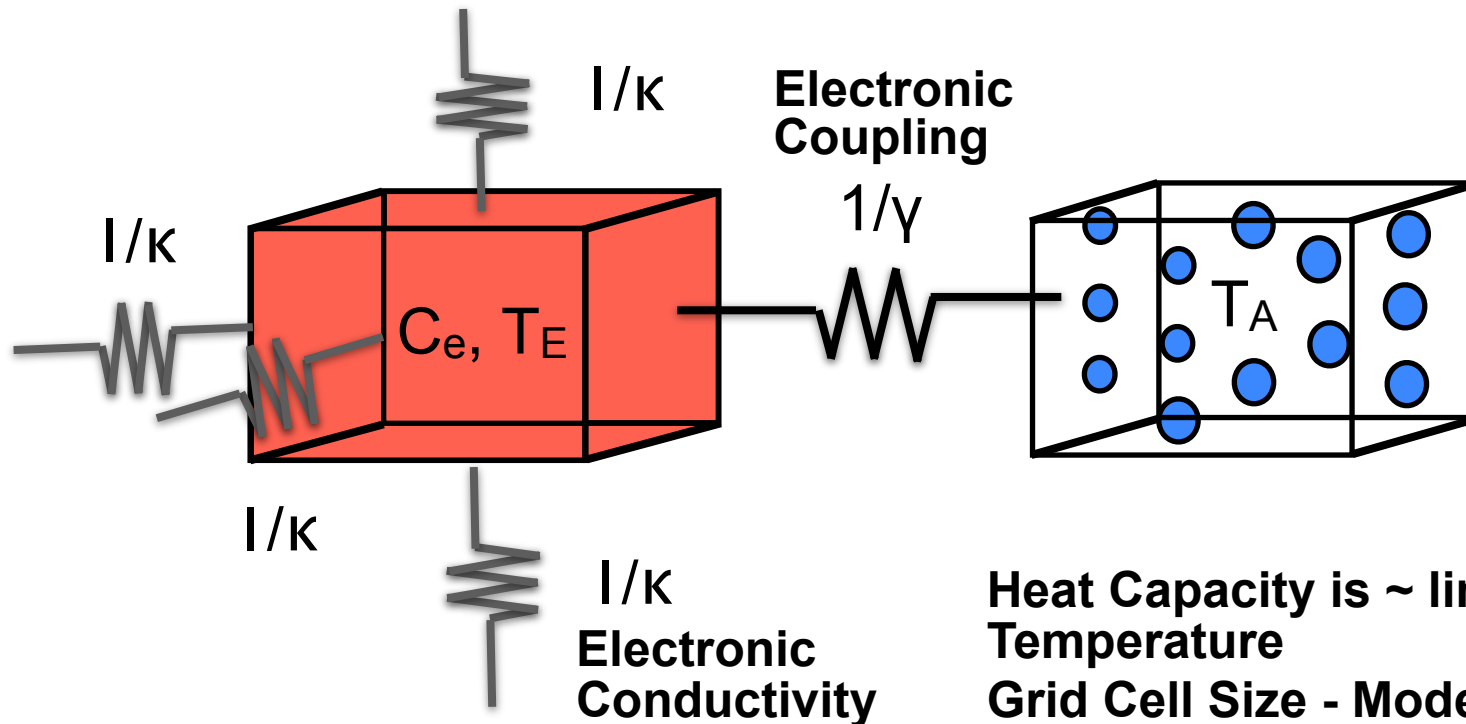
- Caro & Victoria, 1989
 - Fixed Constant Uniform T_e
- Rutherford & Duffy, 2007
 - Spatial and Temporal Variation in T_e
- Phillips & Crozier, 2009
 - Energy Conserving
 - Provided in LAMMPS



Finite Element Mesh Coupled to atoms by inhomogeneous Langevin Thermostat

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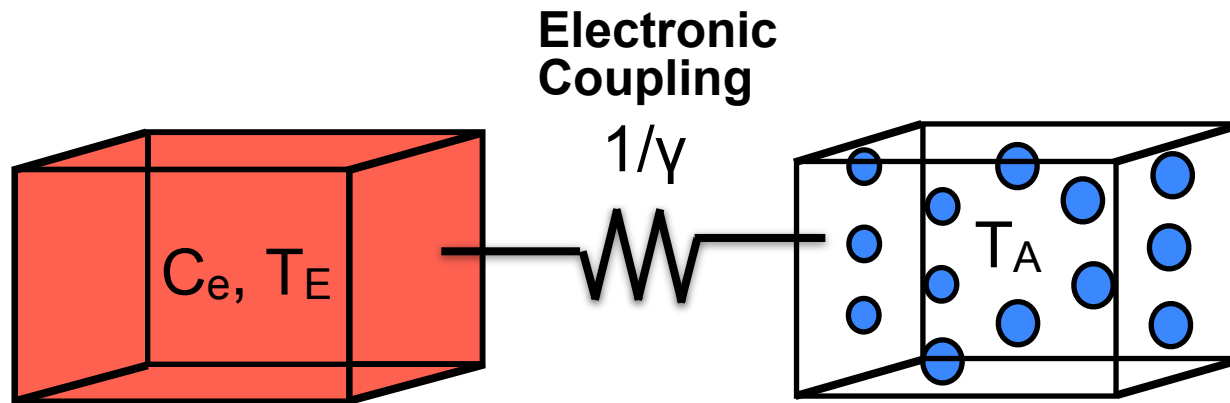
Standard Model - Metallic Gas



Heat Capacity is ~ linear with Temperature
Grid Cell Size - Model Parameter
Electronic Coupling is small
Electric Conductivity is high

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Insulator Model



Heat Capacity is ~ Step function with Temperature

Electronic Conductivity ~ Negligible

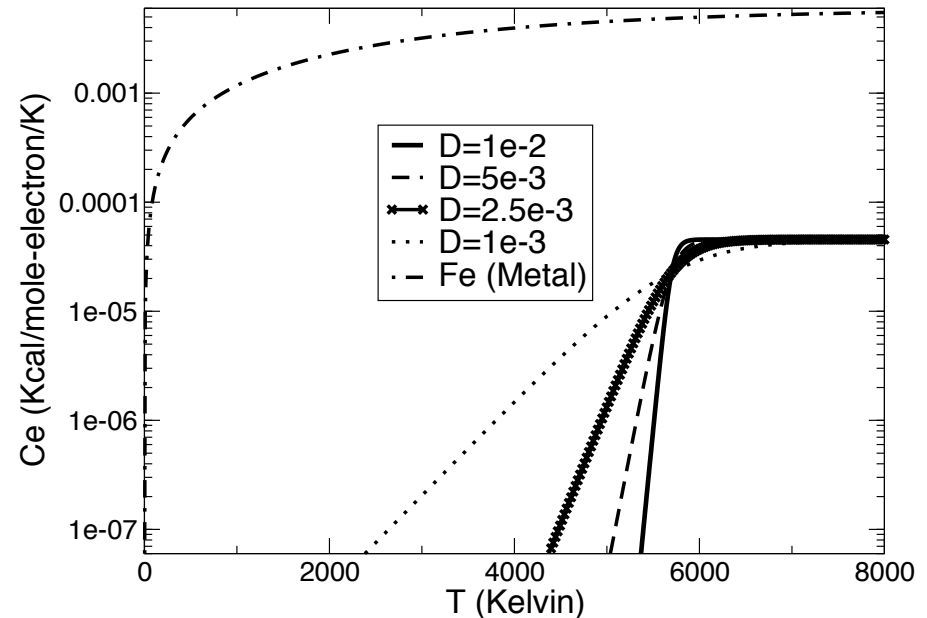
Grid Cell Size ~ Local Excitation Size

Electronic Coupling is High

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Physics Parameters

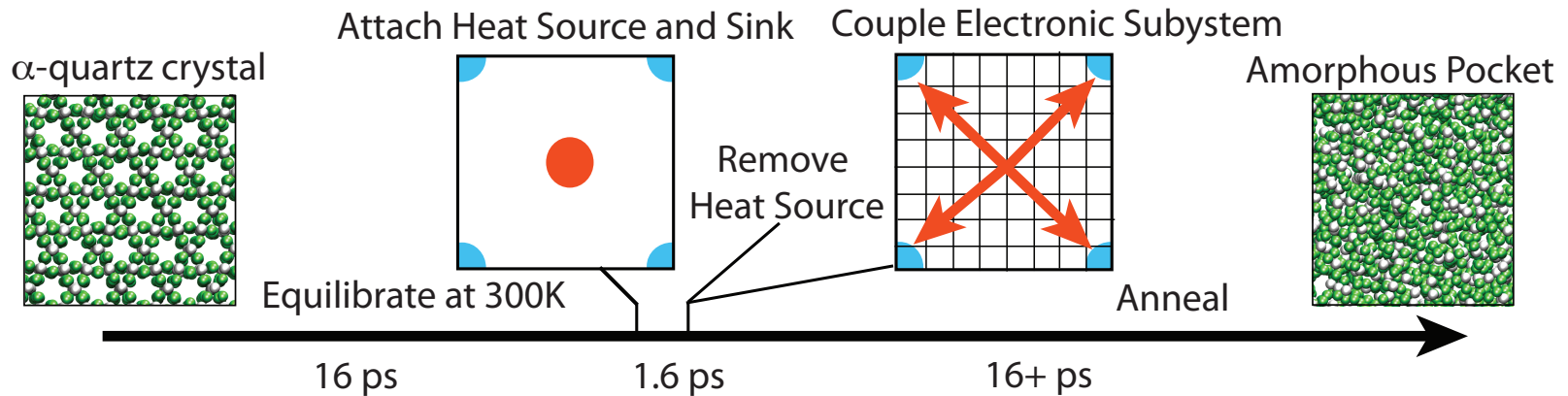
- Heat Capacity, C_e - DFT calculation on 36 atom super cell
- Electron-ion coupling, $\Upsilon_p = m/\tau$, $\tau = 20\text{-}200$ fs.
- Excitation cell size - ?
- D, step softening parameter - ?



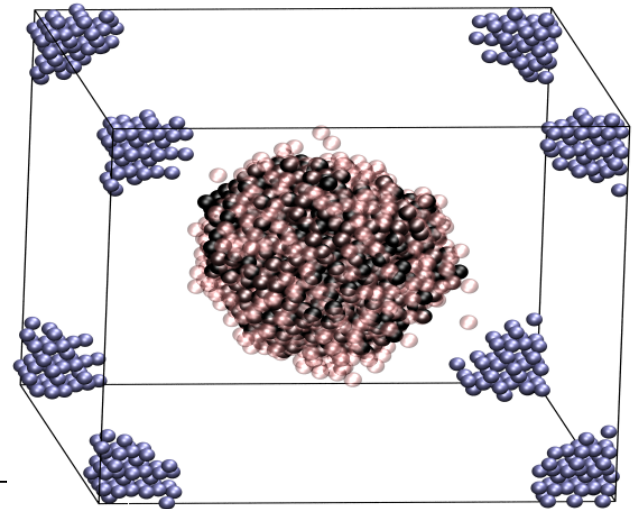
$$C_e(T) = \frac{C_{e,\infty}}{2} * (1 + \tanh(D * (T - T_{threshold})))$$

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Testing the Influence of Models



- **SiO₂ modeled by BKS interaction potential**
- **65,000 atom system (20x20x19 primitive cells)**
- **14.3 keV deposited into spherical region**



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Different models of electronic subsystem

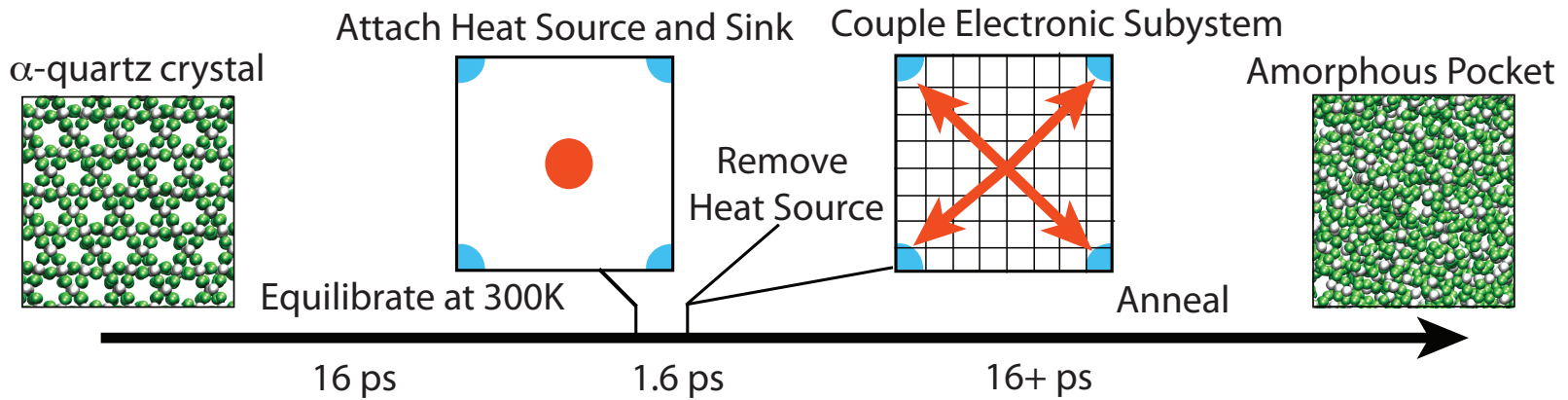
- None
 - “Short-Circuit”
 - Insulator model
 - different size excitation cell
 - more or less tightly coupled
 - softened step function
 - Metallic Model (Fe)
 - “Hot” vs “Cold” Electronic Subsystem
-

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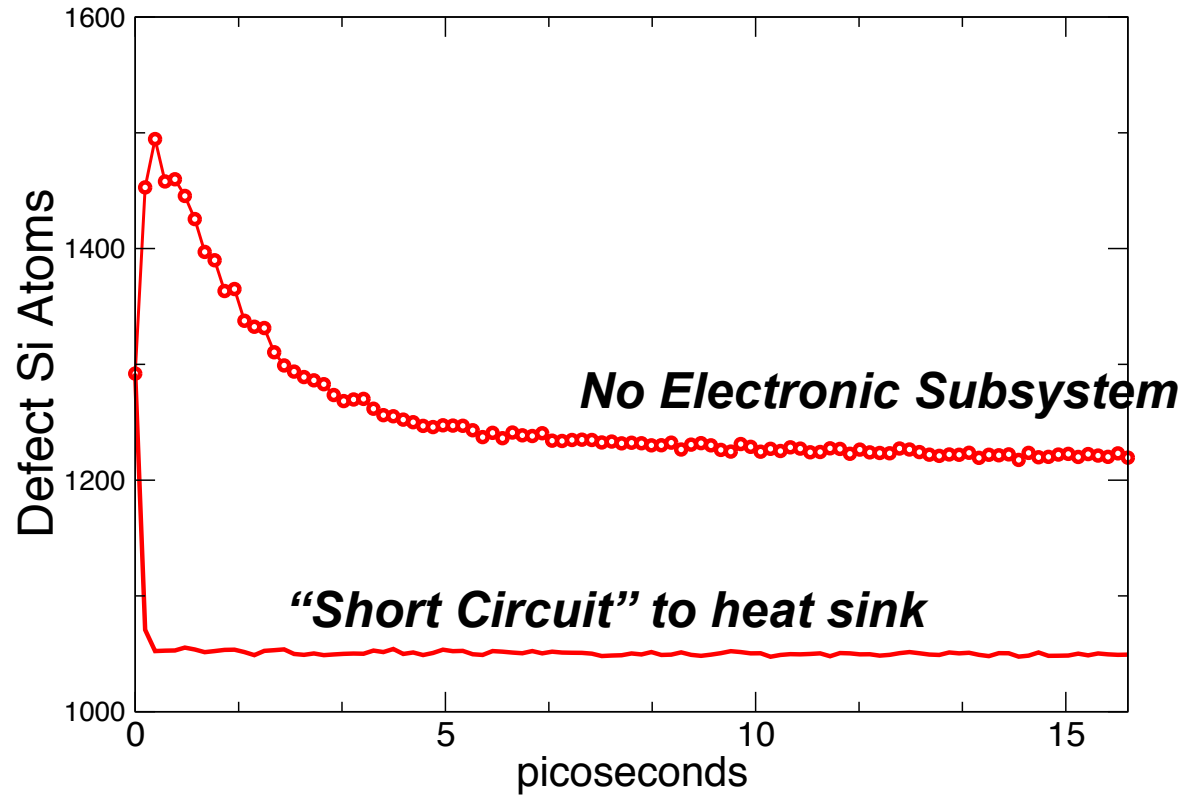
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Defects identified by a local bond order analysis

$$\alpha_j = q_8(i) \cdot q_8(j)$$

$$q_8(i) = \frac{1}{N_b(i)} \sum_{j=1}^{N_b(i)} Y_{8m}(\hat{r}_{ij})$$



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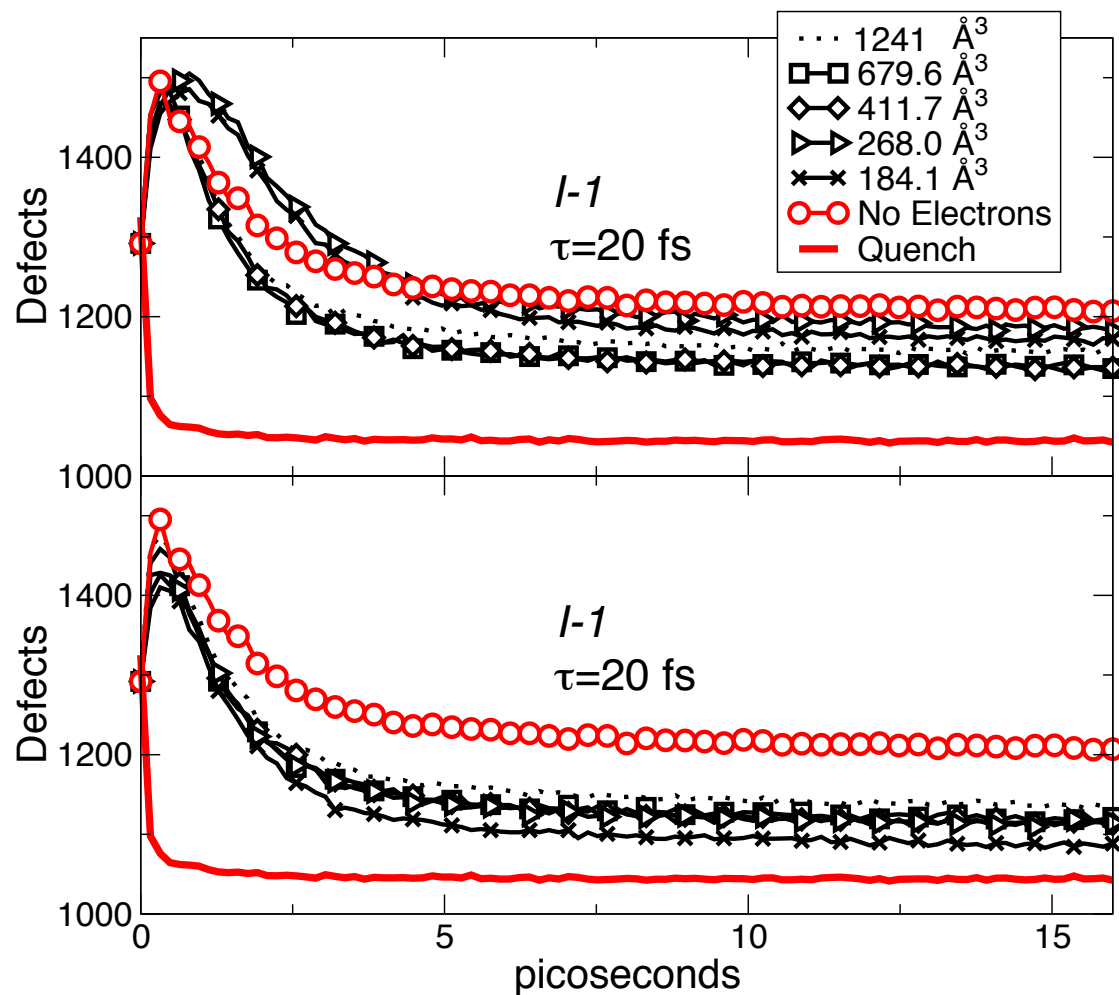
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Excitation cell size

Excitation Cell
Size effect the
system



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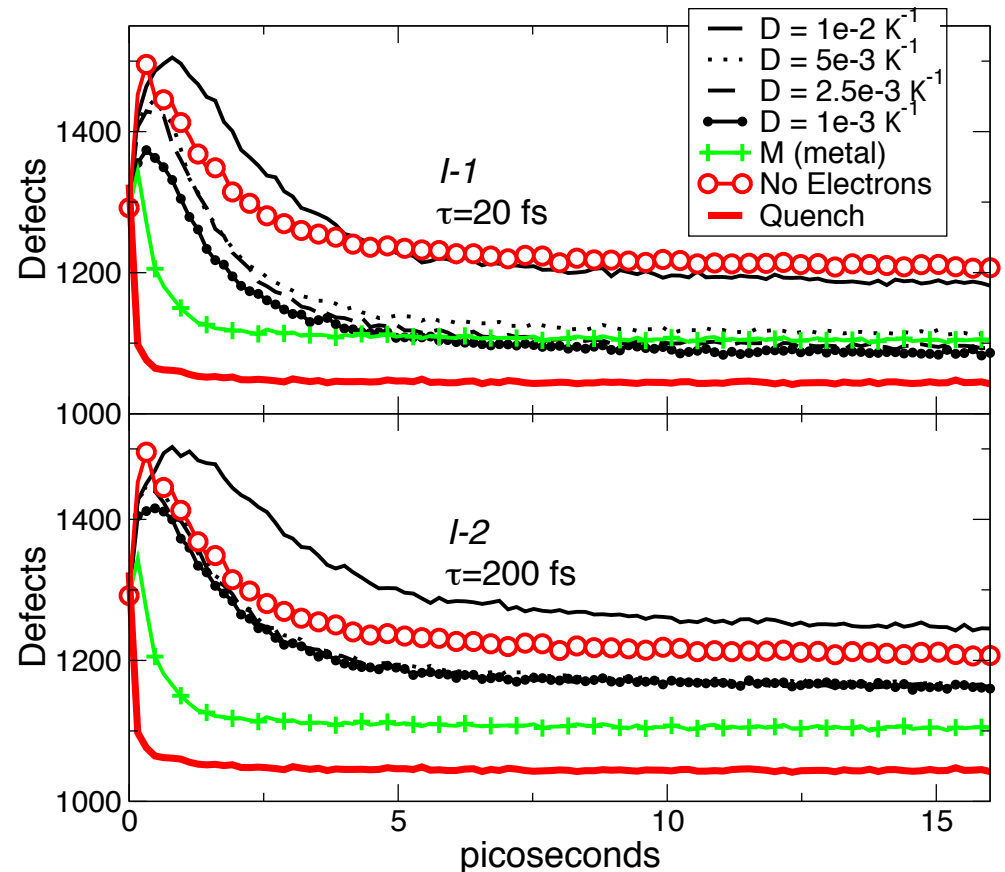
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Influence of D & τ

Ranged from damage similar to a *metallic electronic subsystem* to *no electronic subsystem* at all.



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Conclusions

- Important to include models of the modes of heat transport!
- The coarse model of the electronic subsystem is important. *An Insulator model acts very different from a Metal model.*
- Refined physics parameters are needed.

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